SWITCHMODE™ Pulse Width Modulation Control Circuit

The TL494 is a fixed frequency, pulse width modulation control circuit designed primarily for SWITCHMODE power supply control.

Features

- Complete Pulse Width Modulation Control Circuitry
- On-Chip Oscillator with Master or Slave Operation
- On-Chip Error Amplifiers
- On-Chip 5.0 V Reference
- Adjustable Deadtime Control
- Uncommitted Output Transistors Rated to 500 mA Source or Sink
- Output Control for Push-Pull or Single-Ended Operation
- Undervoltage Lockout
- NCV Prefix for Automotive and Other Applications Requiring Site and Control Changes
- Pb-Free Packages are Available*

MAXIMUM RATINGS (Full operating ambient temperature range applies, unless otherwise noted.)

Rating	Symbol	Value	Unit
Power Supply Voltage	V _{CC}	42	V
Collector Output Voltage	V _{C1} , V _{C2}	42	V
Collector Output Current (Each transistor) (Note 1)	I _{C1} , I _{C2}	500	mA
Amplifier Input Voltage Range	V _{IR}	-0.3 to +42	V
Power Dissipation @ T _A ≤ 45°C	P _D	1000	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	80	°C/W
Operating Junction Temperature	T_J	125	°C
Storage Temperature Range	T _{stg}	-55 to +125	°C
Operating Ambient Temperature Range TL494B TL494C TL494I NCV494B	T _A	-40 to +125 0 to +70 -40 to +85 -40 to +125	°C
Derating Ambient Temperature	T _A	45	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

Maximum thermal limits must be observed.



ON Semiconductor®

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MARKING DIAGRAMS



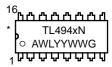
SOIC-16 D SUFFIX CASE 751B





х

PDIP-16 N SUFFIX CASE 648

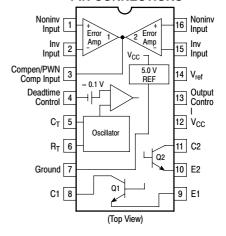


= B, C or I

A = Assembly Location

WL = Wafer Lot
 YY, Y = Year
 WW, W = Work Week
 G = Pb-Free Package

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

^{*}This marking diagram also applies to NCV494.

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Тур	Max	Unit
Power Supply Voltage	V _{CC}	7.0	15	40	V
Collector Output Voltage	V _{C1} , V _{C2}	-	30	40	V
Collector Output Current (Each transistor)	I _{C1} , I _{C2}	-	-	200	mA
Amplified Input Voltage	V _{in}	-0.3	-	V _{CC} – 2.0	V
Current Into Feedback Terminal	I _{fb}	-	-	0.3	mA
Reference Output Current	I _{ref}	-	-	10	mA
Timing Resistor	R _T	1.8	30	500	kΩ
Timing Capacitor	C _T	0.0047	0.001	10	μF
Oscillator Frequency	f _{osc}	1.0	40	200	kHz

ELECTRICAL CHARACTERISTICS (V_{CC} = 15 V, C_T = 0.01 μF, R_T = 12 kΩ, unless otherwise noted.) For typical values T_A = 25°C, for min/max values T_A is the operating ambient temperature range that applies, unless otherwise noted.

Characteristics	Symbol	Min	Тур	Max	Unit
REFERENCE SECTION		•	•	•	•
Reference Voltage (I _O = 1.0 mA)	V _{ref}	4.75	5.0	5.25	V
Line Regulation (V _{CC} = 7.0 V to 40 V)	Reg _{line}	-	2.0	25	mV
Load Regulation (I _O = 1.0 mA to 10 mA)	Reg _{load}	-	3.0	15	mV
Short Circuit Output Current (V _{ref} = 0 V)	I _{sc}	15	35	75	mA
OUTPUT SECTION	<u>.</u>				
Collector Off–State Current (V _{CC} = 40 V, V _{CE} = 40 V)	I _{C(off)}	_	2.0	100	μА
Emitter Off–State Current V _{CC} = 40 V, V _C = 40 V, V _E = 0 V)	I _{E(off)}	-	_	-100	μА
Collector–Emitter Saturation Voltage (Note 2) Common–Emitter ($V_E = 0 \text{ V}, I_C = 200 \text{ mA}$) Emitter–Follower ($V_C = 15 \text{ V}, I_E = -200 \text{ mA}$)	V _{sat(C)} V _{sat(E)}	_ _	1.1 1.5	1.3 2.5	V
Output Control Pin Current Low State ($V_{OC} \le 0.4 \text{ V}$) High State ($V_{OC} = V_{ref}$)	loc _L loch	- -	10 0.2	_ 3.5	μA mA
Output Voltage Rise Time Common–Emitter (See Figure 12) Emitter–Follower (See Figure 13)	t _r	- -	100 100	200 200	ns
Output Voltage Fall Time Common–Emitter (See Figure 12) Emitter–Follower (See Figure 13)	t _f	- -	25 40	100 100	ns

^{2.} Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.

ELECTRICAL CHARACTERISTICS (V_{CC} = 15 V, C_T = 0.01 μ F, R_T = 12 $k\Omega$, unless otherwise noted.) For typical values T_A = 25°C, for min/max values T_A is the operating ambient temperature range that applies, unless otherwise noted.

Characteristics	Symbol	Min	Тур	Max	Unit
ERROR AMPLIFIER SECTION			•	-	
Input Offset Voltage (V _{O (Pin 3)} = 2.5 V)	V _{IO}	_	2.0	10	mV
Input Offset Current (V _{O (Pin 3)} = 2.5 V)	I _{IO}	-	5.0	250	nA
Input Bias Current (V _{O (Pin 3)} = 2.5 V)	I _{IB}	-	-0.1	-1.0	μΑ
Input Common Mode Voltage Range (V _{CC} = 40 V, T _A = 25°C)	V _{ICR}	_	0.3 to V _{CC} -2	2.0	V
Open Loop Voltage Gain (Δ V $_{O}$ = 3.0 V, V $_{O}$ = 0.5 V to 3.5 V, R $_{L}$ = 2.0 k Ω)	A _{VOL}	70	95	-	dB
Unity–Gain Crossover Frequency (V_0 = 0.5 V to 3.5 V, R_L = 2.0 k Ω)	f _C _	-	350	_	kHz
Phase Margin at Unity–Gain (V_0 = 0.5 V to 3.5 V, R_L = 2.0 k Ω)	φ _m	-	65	_	deg.
Common Mode Rejection Ratio (V _{CC} = 40 V)	CMRR	65	90	_	dB
Power Supply Rejection Ratio (ΔV_{CC} = 33 V, V_{O} = 2.5 V, R_{L} = 2.0 k Ω)	PSRR	-	100	_	dB
Output Sink Current (V _{O (Pin 3)} = 0.7 V)	I _{O-}	0.3	0.7	_	mA
Output Source Current (V _{O (Pin 3)} = 3.5 V)	I _O +	2.0	-4.0	_	mA
PWM COMPARATOR SECTION (Test Circuit Figure 11)			1	· L	· L
Input Threshold Voltage (Zero Duty Cycle)	V_{TH}	-	2.5	4.5	V
Input Sink Current (V _(Pin 3) = 0.7 V)	I _I _	0.3	0.7	-	mA
DEADTIME CONTROL SECTION (Test Circuit Figure 11)					•
Input Bias Current (Pin 4) (V _{Pin 4} = 0 V to 5.25 V)	I _{IB (DT)}	-	-2.0	-10	μΑ
Maximum Duty Cycle, Each Output, Push–Pull Mode ($V_{Pin~4}=0~V,~C_{T}=0.01~\mu F,~R_{T}=12~k\Omega$) ($V_{Pin~4}=0~V,~C_{T}=0.001~\mu F,~R_{T}=30~k\Omega$)	DC _{max}	45 -	48 45	50 50	%
Input Threshold Voltage (Pin 4) (Zero Duty Cycle) (Maximum Duty Cycle)	V _{th}	_ 0	2.8	3.3	V
OSCILLATOR SECTION					
Frequency ($C_T = 0.001 \mu F$, $R_T = 30 k\Omega$)	f _{osc}	_	40	_	kHz
Standard Deviation of Frequency* ($C_T = 0.001 \mu F, R_T = 30 k\Omega$)	of _{osc}	_	3.0	_	%
Frequency Change with Voltage (V _{CC} = 7.0 V to 40 V, T _A = 25°C)	$\Delta f_{OSC} (\Delta V)$	_	0.1	_	%
Frequency Change with Temperature ($\Delta T_A = T_{low}$ to T_{high}) ($C_T = 0.01 \ \mu F, \ R_T = 12 \ k\Omega$)	$\Delta f_{\rm osc} (\Delta T)$	-	-	12	%
UNDERVOLTAGE LOCKOUT SECTION				1	
Turn–On Threshold (V _{CC} increasing, I _{ref} = 1.0 mA)	V_{th}	5.5	6.43	7.0	V
TOTAL DEVICE	L		-1	L	·
Standby Supply Current (Pin 6 at V_{ref} , All other inputs and outputs open) (V_{CC} = 15 V) (V_{CC} = 40 V)	Icc	<u>-</u>	5.5 7.0	10 15	mA
Average Supply Current $(C_T = 0.01 \mu F, R_T = 12 k\Omega, V_{(Pin 4)} = 2.0 V)$ $(V_{CC} = 15 V)$ (See Figure 12)		_	7.0	-	mA

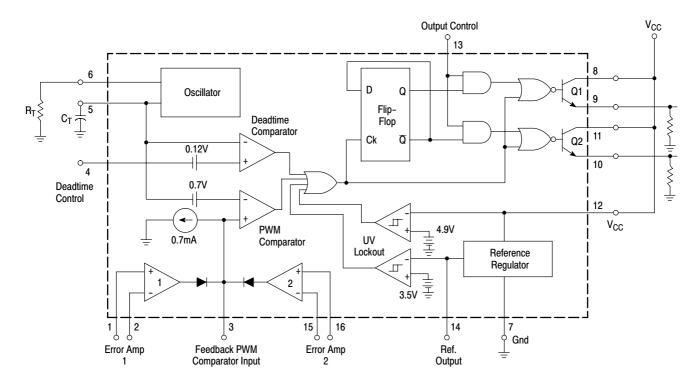
^{*} Standard deviation is a measure of the statistical distribution about the mean as derived from the formula, $\sigma = \sqrt{\frac{N}{\sum (X_n - \overline{X})^2}}$

ORDERING INFORMATION

Device	Package	Shipping [†]
TL494BD	SOIC-16	48 Units / Rail
TL494BDG	SOIC-16 (Pb-Free)	48 Units / Rail
TL494BDR2	SOIC-16	2500 Tape & Reel
TL494BDR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
TL494CD	SOIC-16	48 Units / Rail
TL494CDG	SOIC-16 (Pb-Free)	48 Units / Rail
TL494CDR2	SOIC-16	2500 Tape & Reel
TL494CDR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
TL494CN	PDIP-16	25 Units / Rail
TL494CNG	PDIP-16 (Pb-Free)	25 Units / Rail
TL494IN	PDIP-16	25 Units / Rail
TL494ING	PDIP-16 (Pb-Free)	25 Units / Rail
NCV494BDR2*	SOIC-16	2500 Tape & Reel
NCV494BDR2G*	SOIC-16 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specifications Brochure, BRD8011/D. *NCV494: T_{low} = -40°C, T_{high} = +125°C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.



This device contains 46 active transistors.

Figure 1. Representative Block Diagram

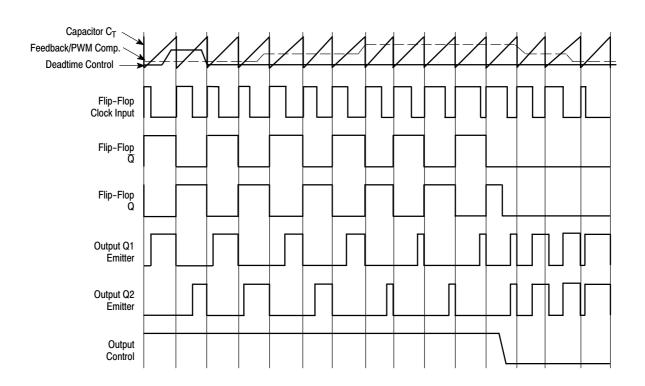


Figure 2. Timing Diagram

APPLICATIONS INFORMATION

Description

The TL494 is a fixed–frequency pulse width modulation control circuit, incorporating the primary building blocks required for the control of a switching power supply. (See Figure 1.) An internal–linear sawtooth oscillator is frequency– programmable by two external components, R_T and C_T . The approximate oscillator frequency is determined by:

$$f_{OSC} \approx \frac{1.1}{R_T \bullet C_T}$$

For more information refer to Figure 3.

Output pulse width modulation is accomplished by comparison of the positive sawtooth waveform across capacitor C_T to either of two control signals. The NOR gates, which drive output transistors Q1 and Q2, are enabled only when the flip–flop clock–input line is in its low state. This happens only during that portion of time when the sawtooth voltage is greater than the control signals. Therefore, an increase in control–signal amplitude causes a corresponding linear decrease of output pulse width. (Refer to the Timing Diagram shown in Figure 2.)

The control signals are external inputs that can be fed into the deadtime control, the error amplifier inputs, or the feedback input. The deadtime control comparator has an effective 120 mV input offset which limits the minimum output deadtime to approximately the first 4% of the sawtooth–cycle time. This would result in a maximum duty cycle on a given output of 96% with the output control grounded, and 48% with it connected to the reference line. Additional deadtime may be imposed on the output by setting the deadtime–control input to a fixed voltage, ranging between 0 V to 3.3 V.

Functional Table

Input/Output Controls	Output Function	$\frac{f_{out}}{f_{osc}} =$
Grounded	Single-ended PWM @ Q1 and Q2	1.0
@ V _{ref}	Push-pull Operation	0.5

The pulse width modulator comparator provides a means for the error amplifiers to adjust the output pulse width from the maximum percent on—time, established by the deadtime control input, down to zero, as the voltage at the feedback pin varies from 0.5 V to 3.5 V. Both error amplifiers have a

common mode input range from -0.3~V to $(V_{CC}-2V)$, and may be used to sense power–supply output voltage and current. The error–amplifier outputs are active high and are ORed together at the noninverting input of the pulse–width modulator comparator. With this configuration, the amplifier that demands minimum output on time, dominates control of the loop.

When capacitor C_T is discharged, a positive pulse is generated on the output of the deadtime comparator, which clocks the pulse-steering flip-flop and inhibits the output transistors, Q1 and Q2. With the output-control connected to the reference line, the pulse-steering flip-flop directs the modulated pulses to each of the two output transistors alternately for push-pull operation. The output frequency is equal to half that of the oscillator. Output drive can also be taken from Q1 or Q2, when single-ended operation with a maximum on-time of less than 50% is required. This is desirable when the output transformer has a ringback winding with a catch diode used for snubbing. When higher output-drive currents are required for single-ended operation, Q1 and Q2 may be connected in parallel, and the output-mode pin must be tied to ground to disable the flip-flop. The output frequency will now be equal to that of the oscillator.

The TL494 has an internal 5.0 V reference capable of sourcing up to 10 mA of load current for external bias circuits. The reference has an internal accuracy of $\pm 5.0\%$ with a typical thermal drift of less than 50 mV over an operating temperature range of 0° to 70° C.

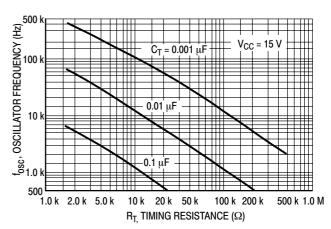


Figure 3. Oscillator Frequency versus
Timing Resistance

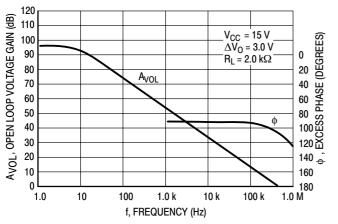


Figure 4. Open Loop Voltage Gain and Phase versus Frequency

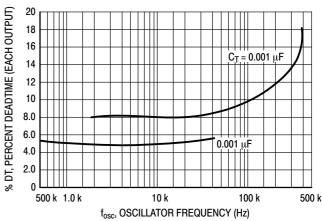


Figure 5. Percent Deadtime versus Oscillator Frequency

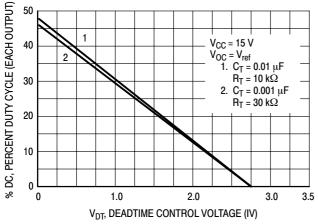


Figure 6. Percent Duty Cycle versus Deadtime Control Voltage

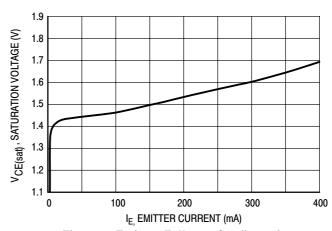


Figure 7. Emitter–Follower Configuration
Output Saturation Voltage versus
Emitter Current

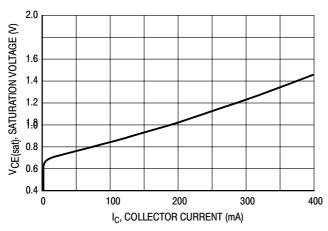


Figure 8. Common–Emitter Configuration
Output Saturation Voltage versus
Collector Current

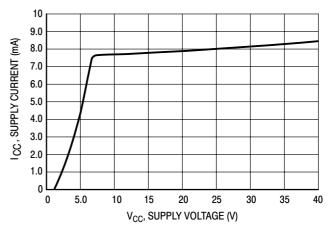


Figure 9. Standby Supply Current versus Supply Voltage

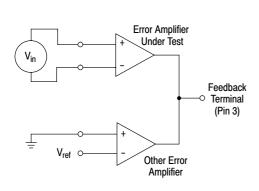


Figure 10. Error-Amplifier Characteristics

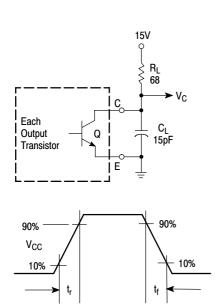


Figure 12. Common–Emitter Configuration
Test Circuit and Waveform

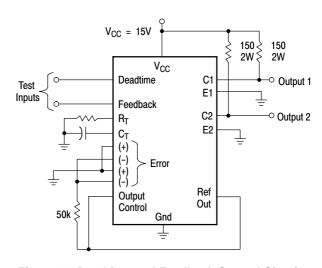


Figure 11. Deadtime and Feedback Control Circuit

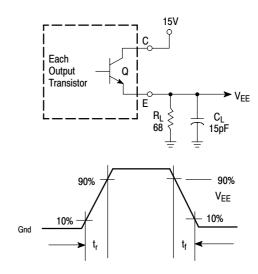


Figure 13. Emitter–Follower Configuration
Test Circuit and Waveform

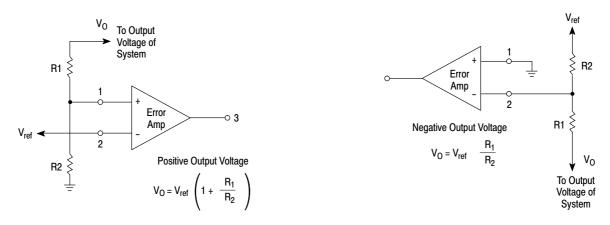


Figure 14. Error-Amplifier Sensing Techniques

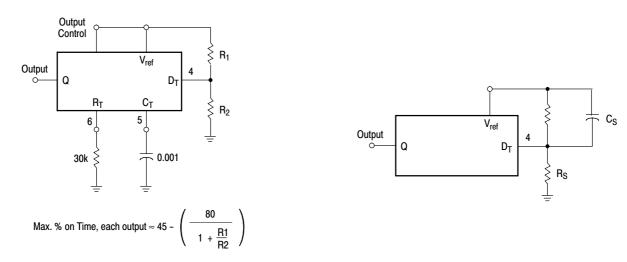


Figure 15. Deadtime Control Circuit

Figure 16. Soft-Start Circuit

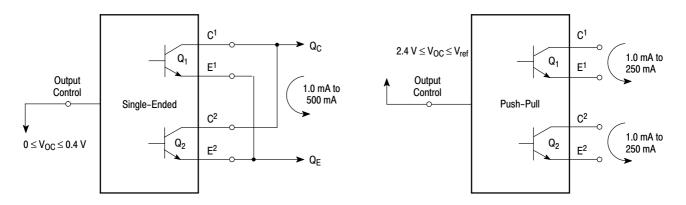


Figure 17. Output Connections for Single-Ended and Push-Pull Configurations

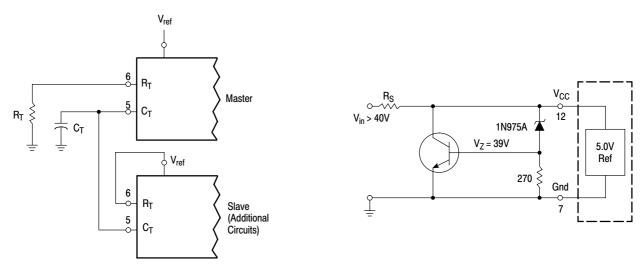


Figure 18. Slaving Two or More Control Circuits

Figure 19. Operation with V_{in} > 40 V Using External Zener

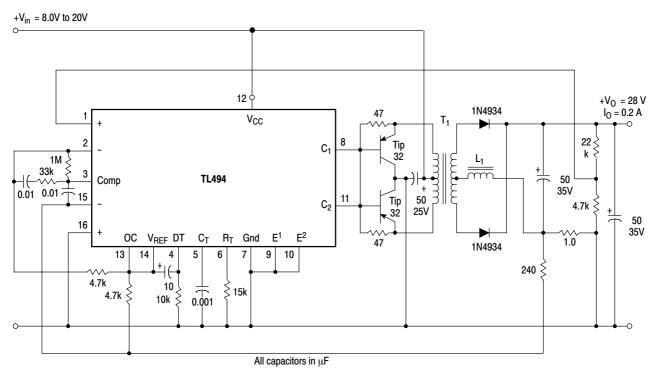


Figure 20. Pulse Width Modulated Push-Pull Converter

Test	Conditions	Results
Line Regulation	V _{in} = 10 V to 40 V	14 mV 0.28%
Load Regulation	$V_{in} = 28 \text{ V}, I_{O} = 1.0 \text{ mA to } 1.0 \text{ A}$	3.0 mV 0.06%
Output Ripple	V _{in} = 28 V, I _O = 1.0 A	65 mV pp P.A.R.D.
Short Circuit Current	V_{in} = 28 V, R_L = 0.1 Ω	1.6 A
Efficiency	V _{in} = 28 V, I _O = 1.0 A	71%

L1 - 3.5 mH @ 0.3 A

T1 - Primary: 20T C.T. #28 AWG Secondary: 12OT C.T. #36 AWG Core: Ferroxcube 1408P-L00-3CB

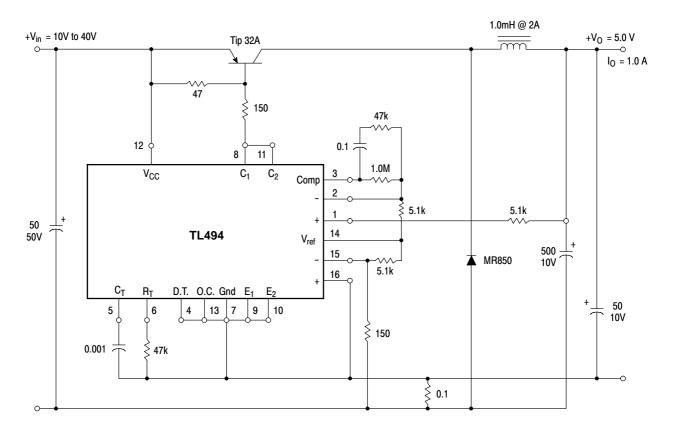
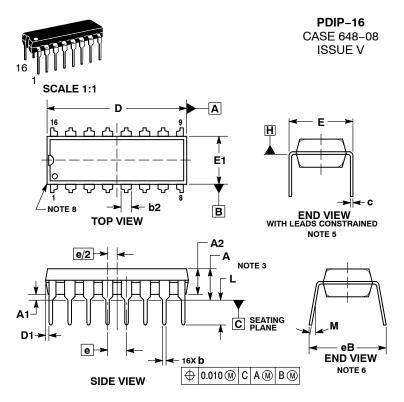


Figure 21. Pulse Width Modulated Step-Down Converter

Test	Conditions	Results	
Line Regulation	V _{in} = 8.0 V to 40 V	3.0 mV 0.01%	
Load Regulation	$V_{in} = 12.6 \text{ V}, I_{O} = 0.2 \text{ mA to } 200 \text{ mA}$	5.0 mV 0.02%	
Output Ripple	V _{in} = 12.6 V, I _O = 200 mA	40 mV pp P.A.R.D.	
Short Circuit Current	$V_{in} = 12.6 \text{ V}, R_L = 0.1 \Omega$	250 mA	
Efficiency	V _{in} = 12.6 V, I _O = 200 mA	72%	



DATE 22 APR 2015

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

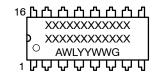
- DIMENSIONING AND TOLERANGING FER ASME 114-3M, 1994
 CONTROLLING DIMENSION: INCHES.

 DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.

 DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH
 OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE
 NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR
- DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE
- DIMENSION 8B IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
 DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
 PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE
- CORNERS).

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	TYP	1.52	TYP
С	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54 BSC	
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
M		10°		10°

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code

= Assembly Location

WL = Wafer Lot YY = Year

WW = Work Week

G = Pb-Free Package

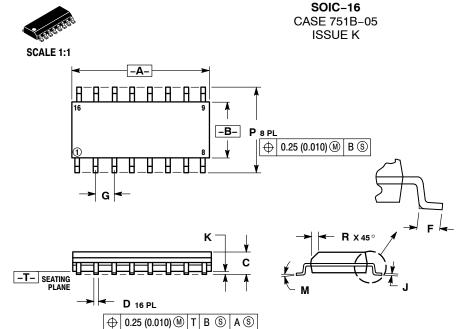
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1	:	STYLE 2	:
PIN 1.	CATHODE	PIN 1.	COMMON DRAIN
2.	CATHODE	2.	COMMON DRAIN
3.	CATHODE	3.	COMMON DRAIN
4.	CATHODE	4.	COMMON DRAIN
5.	CATHODE	5.	COMMON DRAIN
6.	CATHODE	6.	COMMON DRAIN
7.	CATHODE	7.	COMMON DRAIN
8.	CATHODE	8.	COMMON DRAIN
9.	ANODE	9.	GATE
10.	ANODE	10.	SOURCE
11.	ANODE	11.	GATE
12.	ANODE	12.	SOURCE
13.	ANODE	13.	GATE
14.	ANODE	14.	SOURCE
15.	ANODE	15.	GATE
16.	ANODE	16.	SOURCE

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DESCRIPTION:	PDIP-16		PAGE 1 OF 1

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MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	COL DEDING	FOOTPRINT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	3 FOOTPRINT
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		5.40 →
									,.40
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 <
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	T)		. 🔲 1	16
3.	DRAIN, #2	3.		3.	COMMON DRAIN (OUTPU			↓ └─ ─ '	" 🗀
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	.,		- —	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	T)	16	5X T	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		0.5	iii I	' <u> </u>
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU		0.0	56	1
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	.,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPU	T)			
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	,			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPU	T)			— V PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU				<u>+-+</u> -
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH	•			
								8	9 + - + -
								— -	_ · · · · · · · · · · · · · · · · · · ·
									DIMENSIONS, MILLIMETERS
									DIMENSIONS: MILLIMETERS

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